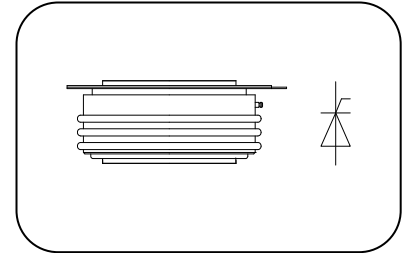




Features

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses
- Short turn-off time
- Hermetic metal cases with ceramic insulators

$I_{T(AV)}$ **1200A**
 V_{DRM}/V_{RRM} **1100~1400V**
 t_q **10~16μs**
 I_{TSM} **18kA**



Typical Applications

- Inductive heating
- Electronic welders
- Self-commutated inverters
- AC motor speed control
- General power switching applications

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_j(^{\circ}C)$	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled, $T_C=55^{\circ}C$	125		1200	1520	A
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	$V_{DRM} \& V_{RRM}, t_p=10ms$ $V_{DSM} \& V_{RSM} = V_{DRM} \& V_{RRM} + 100V$	125	1100		1400	V
I_{DRM} I_{RRM}	Repetitive peak off-state current Repetitive peak reverse current	$V_D = V_{DRM}$ $V_R = V_{RRM}$	125			100	mA
I_{TSM}	Surge on-state current	10ms half sine wave	125			18	kA
I^2t	I^2t for fusing coordination	$V_R = 0.6V_{RRM}$				1620	$A^2s \cdot 10^3$
V_{TO}	Threshold voltage		125			1.63	V
r_T	On-state slop resistance					0.25	mΩ
V_{TM}	Peak on-state voltage	$I_{TM}=3000A, F=26kN$	25			3.20	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			1000	V/μs
di/dt	Critical rate of rise of on-state current	$V_{DM}= 67\%V_{DRM}$ $I_{TM}=(2-3)I_{T(AV)}$, $t=5s$, Gate pulse $t_r \leq 0.5\mu s$ $I_{GM}=1.5A$ $f=50Hz$	125			600	A/μs
Q_{rr}	Recovery charge	$I_{TM}=1200A, t_p=1000\mu s$, $di/dt=-20A/\mu s, V_R=100V$	125		105	120	μC
t_q	Circuit commutated turn-off time	$I_{TM}=1200A, t_p=1000\mu s, V_R = 100V$ $dv/dt=30V/\mu s, di/dt=-20A/\mu s$	125	10		16	μs
I_{GT}	Gate trigger current	$V_A=12V, I_A=1A$	25	30		300	mA
V_{GT}	Gate trigger voltage			0.8		3.0	V
I_H	Holding current			20		400	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125			0.3	V
$R_{th(j-c)}$	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 26kN				0.018	$^{\circ}C/W$
$R_{th(c-h)}$	Thermal resistance case to heat sink					0.004	
F_m	Mounting force			21		30	kN
T_{stg}	Stored temperature			-40		140	$^{\circ}C$
W_t	Weight				600		g
Outline	KT60cT						

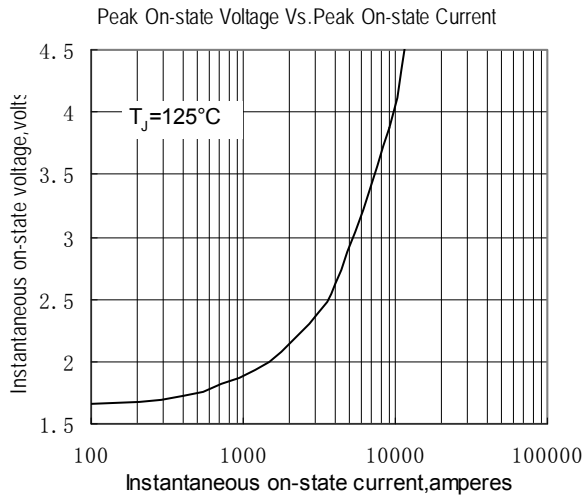


Fig. 1

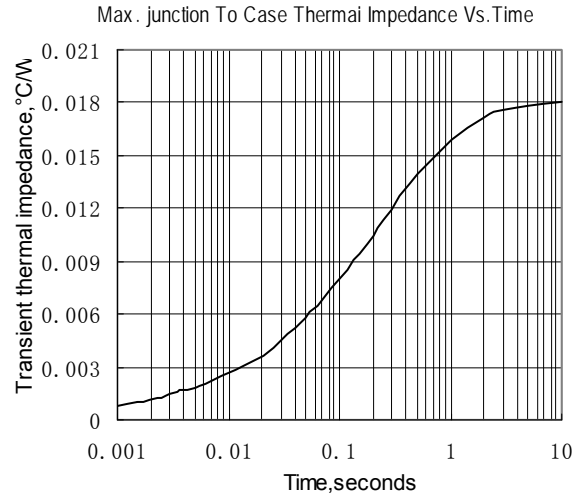


Fig. 2

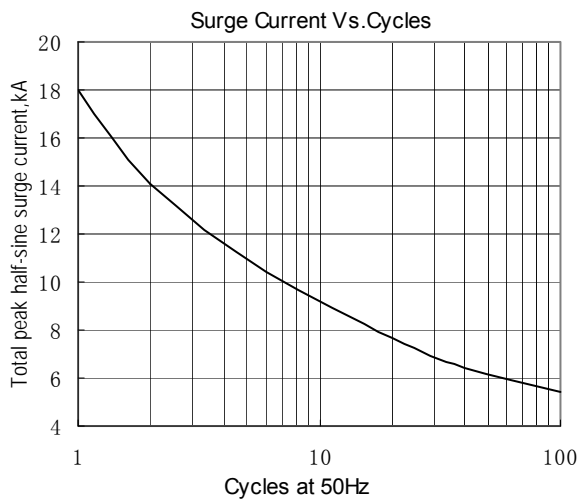


Fig. 3

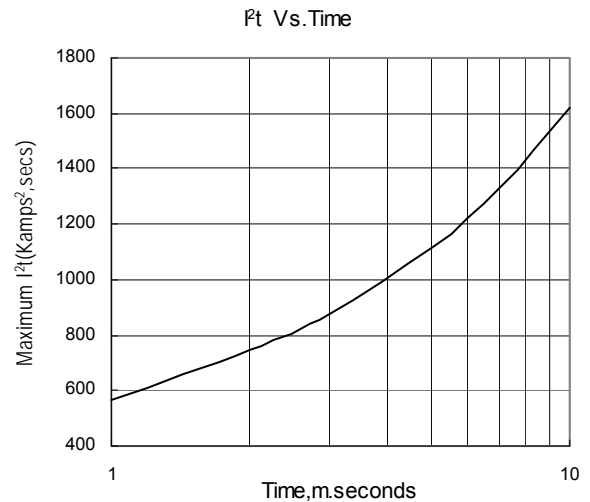


Fig. 4

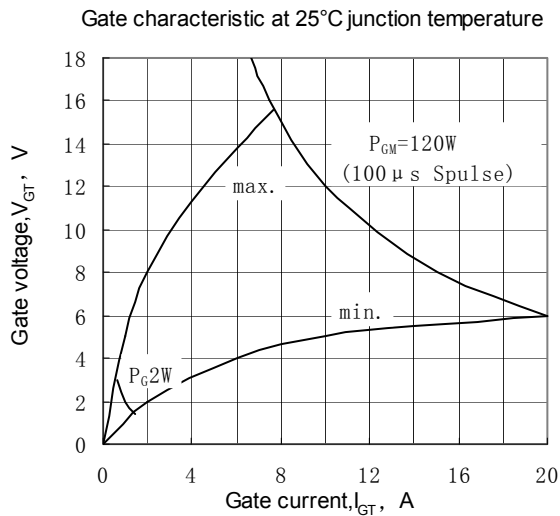


Fig. 5

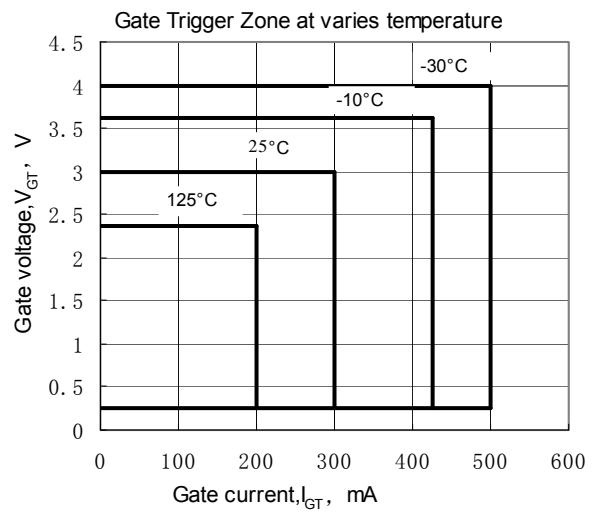
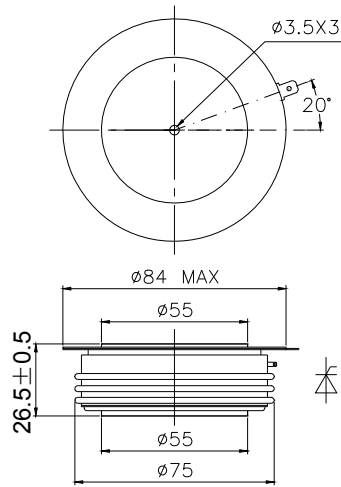


Fig. 6



Outline:

图10-KT60cT



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